

Sem III OTR
EXTC

QP CODE : 542800

(OLD COURSE)

(3 Hours)

Total Marks : 100

- N.B. (1) Question No. 1 is compulsory.
 (2) Attempt any **four** out of remaining **six** questions.
 (3) Make **suitable** assumptions if **required** and **justify** the same.

1. (a) Volume of a certain solid V is calculated using formula $V = 64 \frac{xy^4}{z^2}$ 5
 where x, y & z denote three dimensions. If maximum possible errors in the x, y & z is limited to plus minus 0.001. Estimate the maximum probable error in the calculation of volume if the normal dimension x, y & z are equal to unity.
- (b) Define the operators $\Delta, \nabla, \delta, \mu$ & E . Prove that 5
 i) $2\mu\delta = \Delta + \nabla$ ii) $E = 1 + \Delta$
- (c) Using Picard's method solve 5
 $\frac{dy}{dx} = 1 + xy$ such that $y = 0$ when $x = 0$.
- (d) Derive the equation for Regula - falsi method using geometrical interpretation. 5
2. (a) List the bracketing methods and open methods and find the real root of the equation $xe^x - \cos x = 0$ using Newton-Raphson method correct to three decimal places. 10
- (b) Solve the following equations by Gauss - Seidel method. 10
 $27x + 6y - z = 85, \quad 6x + 15y + 2z = 72, \quad x + y + 54z = 110.$
3. (a) From the following table find the number of students who obtained marks less than 45. 10

Marks	30-40	40-50	50-60	60-70
No. of students	31	42	51	35

- (b) Using Newton's divided difference formula, find the value of $f(9)$ from the following table. 10

x	5	7	11	13	17
$f(x)$	150	392	1452	2366	5202

[TURN OVER

4. (a) Write a program for Lagrange's interpolation method and using this formula, find the value of y when $x = 10$ from the following table.

x	5	6	9	11
y	12	13	14	16

10

- (b) Fit a second degree parabola to the following data:

x	2	4	5	6	8	11
y	18	12	10	8	7	5

10

5. (a) Evaluate $\int_0^6 \frac{dx}{1+x^2}$ by using Trapezoidal, Simpson's $\frac{1^{rd}}{3}$ and Simpson's $\frac{3^{th}}{8}$ rule.

10

- (b) Solve $\frac{dy}{dx} = x^2 + y$ with $x_0 = 0$, $y_0 = 1$ by Euler's modified formula find the value of y when $x = 0.5$ taking $h = 0.25$.

10

6. (a) Solve $\frac{dy}{dx} = x + y^2$ with initial conditions $y(1) = 1.5$ and find y at $x = 1.2$, $x = 1.4$ by Runge - Kutta Method of Fourth Order taking $h = 0.2$.

10

- (b) Solve the following set of equations using Gauss Elimination method.

10

$$2x + y + z = 10, \quad 3x + 2y + 3z = 18, \quad x + 4y + 9z = 16.$$

7. (a) Explain the propagation of errors.

5

- (b) Using Adams - Bashforth method, obtain the solution of $\frac{dy}{dx} = x - y^2$ at $y(0.8)$, given values

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x	0	0.2	0.4	0.6
y	0	0.0200	0.0795	0.1762

- (c) Write a short note on Golden section search.

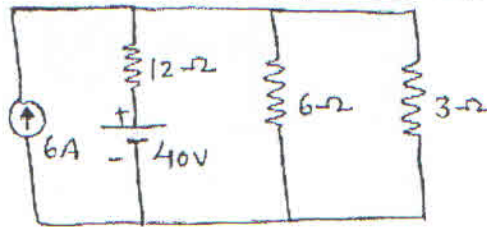
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- NB:** 1) Question No.1 is compulsory.
2) Attempt any four from the remaining questions.
3) Assume suitable data, if required.

1. Attempt any four :

20

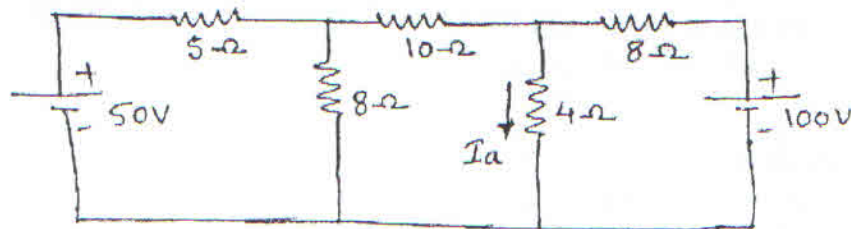
- (a) Using source transformation, replace the network with a single current source and a resistors.



- (b) Define Unilateral and Bilateral element. 05
 (c) Obtain condition for reciprocity for Z parameters. 05
 (d) Define final steady state condition for resistor and capacitor. 05
 (e) Draw pole zero plot for $-S(S+1)/(S+3)(S+2)^2$

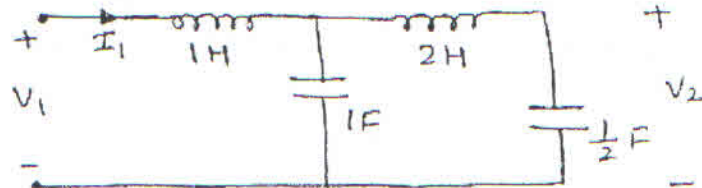
2. (a) Using nodal analysis calculate current I_a in the given network.

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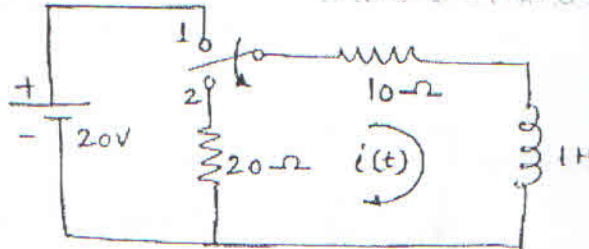
- (b) Find the network functions V_1 / I_1 , V_2 / I_1 , and V_2 / V_1 .

10

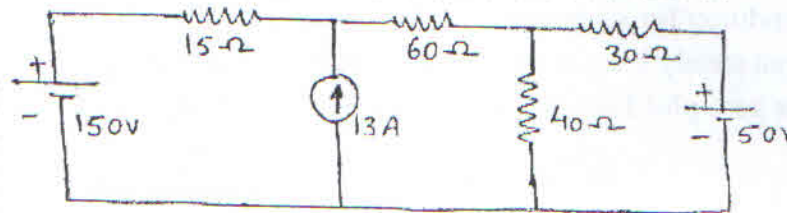


3. (a) Realise the function using Cauer 1 and Cauer II 10
 $Z(s) = (10S^4 + 12S^2 + 1) / (2S^3 + 2S)$

- (b) In the given network switch initially is at position 1, and attains steady state condition. 10
 At $t=0$, it is moved from position 1 to position 2, find the value of $(i, di/dt$ and $d^2i/dt^2)$ at $t > 0^+$.



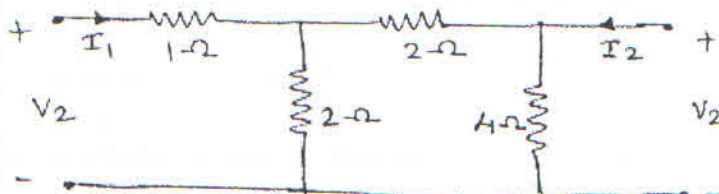
4. (a) Find the current through 30Ω resistor. 10



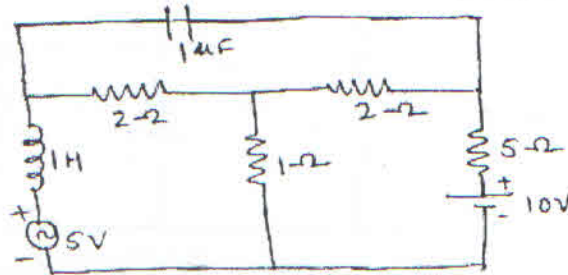
- (b) Test the function is PRF or not 05
 $F(s) = (S^3 + 6S^2 + 7S + 3) / (S^2 + 2S + 1)$

- (c) Test whether the polynomials are Hurwitz or not 10
 (1) $P(s) = 2S^4 + 5S^3 + 5S^2 + 4S + 10$
 (2) $P(s) = S^5 + S^3 + S$

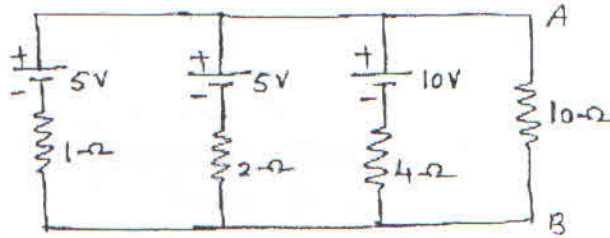
5. (a) Find h parameters for the given network 10



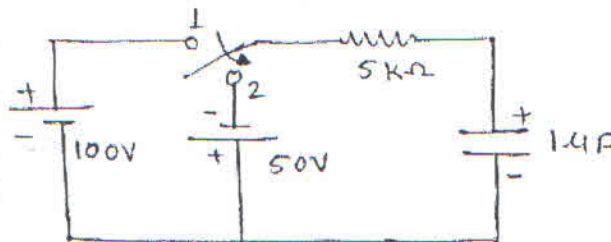
- (b) For the given network draw graph and write down incidence matrix, cut-set matrix and tie-set matrix. 10



6. (a) Determine voltage across AB branch for the given network. 10

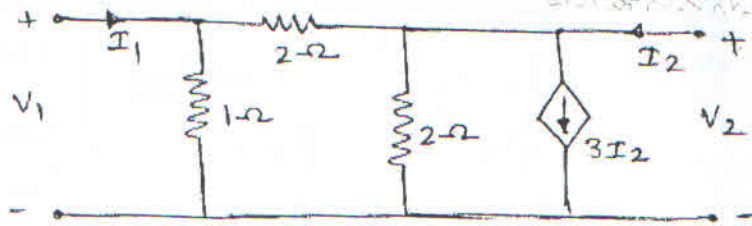


- (b) The switch in the circuit is moved from position 1 to 2 at $t=0$, calculate voltage across capacitor. 10



7. (a) For the given network find Z and ABCD parameters.

10



(b) Draw the Bode plot for the given T.F.

10

$$G(S)H(S) = \frac{10(S + 1)}{S(1 + 0.02S)(1 + 0.002S)}$$

S.E - sem-II (COLD) EXTC

Dt: 24.5.19

QP Code: 544400

(3 Hours)

Total Marks: 100

- N.B. :**
- (1) Question No.1 is **compulsory**.
 - (2) Solve any **four** questions out of remaining **six**.
 - (3) Each questions carries **20 marks**. Equal marks for the subquestions.
 - (4) **Assume** suitable **data** if required.

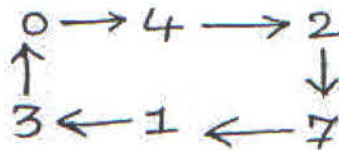
1. (a) Perform $(28)_{10} - (54)_{10}$ using 2's complement method.
- (b) Convert T-FF to D-FF
- (c) Differentiate between Demultiplexer and Decoder.
- (d) Compare PAL and PLA

2. (a) Describe various Binary codes giving examples.
- (b) Minimize following logical function using k-map
 $f(A, B, C, D) = \sum m(1, 3, 5, 8, 9, 11, 15) + d(2, 13)$

3. (a) Design the logic ckt for following logical operations using single decoder and few logic gates.
 (i) 2-I/P EX-OR (ii) 2-I/P EX-NOR
- (b) Explain the term Race Around condition and methods to avoid it.

4. (a) Minimize following logical function using Quine Mc Cluskey method
 $f(A, B, C, D) = \sum m(1, 3, 7, 11, 15) + d(0, 2, 5)$
- (b) (i) Implement $Y = (A+B).(A+C)$ using NOR gates.
 (ii) Using boolean algebraic theorems, prove that,
 $AB + ABC + AB = A$

5. (a) Explain ECL Logic family
- (b) Design synchronous counter for the following counting sequence using MS-JKFFs



6. (a) Describe various characteristics of logic families.
- (b) Draw and explain 3-bit Right shift Register with output waveforms.

Write short notes on

- (i) Multiplexer
- (ii) Universal gates
- (iii) CPLD
- (iv) TTL Logic family

(3 Hours)

[Total Marks : 100

- N.B. :** (1) Question No.1 is compulsory.
 (2) Answer any **Four** questions out of the remaining six questions.
 (3) Figures to the right indicate **full** marks.

1. a) Find Laplace transform of $t \sin 3t \cos t$ 5
 b) Obtain complex form of Fourier series for $f(x) = \sinh(ax)$ in $(-1, 1)$ 5
 c) Show that every square matrix can be uniquely expressed as the scm of a Hermitian and skew- Hermitian matrix. 5
 d) Find the inverse Laplace transformation of $\frac{s^2 + 1}{s^3 + 3s^2 + 2s}$ 5
2. a) Find Laplace transform of $(\int_0^1 e^{-3u} \cos^2(u) du)$ 6
 b) If $A = \begin{bmatrix} 0 & 2b & c \\ a & b & -c \\ a & -b & c \end{bmatrix}$ is orthogonal, Find a, b, c , also Find A^{-1} . 6
 c) Find the Fourier expansion for $f(x) = x^2$ in $(0, 2\pi)$ Hence deduce $\frac{\pi^2}{12} = \frac{1}{1^2} - \frac{1}{2^2} + \frac{1}{3^2} - \frac{1}{4^2} + \dots$ 8
3. a) Test for consistency and solve $2x - 3y + 5z = 1, 3x + y - z = 2, x + 4y - 6z = 1$ 6
 b) Find the Fourier expansion for $f(x) = 4 - x^2$ in $(0, 2)$ 6
 c) Find inverse z-transform of $\frac{3z^2 - 18z + 26}{(z-2)(z-3)(z-4)}, 3 < z < 4$ 8
4. a) Solve Using Laplace transform $[D^2 + 4D + 8] y = 1$ where $y(0) = 0, y'(0) = 1$. 6
 b) Find the Fourier expansion for $f(x) = \left(\frac{3x^2 - 6x + 2\pi^2}{12} \right)$ in $(0, 0\pi)$ 6
 c) Find z- transform of $c^k \sinh(\alpha k), k \geq 0$ 8

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5. a) Find fourier integral representation for 6

$$f(x) = f(x) = \begin{cases} 1-x^2 & \text{for } |x| \leq 1 \\ 0 & \text{for } |x| > 1 \end{cases}$$

- b) Find the two non -singular matrices P and Q such that 6

PAQ is in normal form where $A = \begin{bmatrix} 1 & 2 & -2 \\ -1 & 3 & 0 \\ 0 & -2 & 1 \end{bmatrix}$ hence find Rank and A^{-1}

- c) Obtain Half range sine series $f(x) = xsinx$ in $(0, \pi)$. Hence deduce 8

$$\frac{\pi^2}{8\sqrt{2}} = \frac{1}{1^2} - \frac{1}{3^2} + \frac{1}{5^2} - \frac{1}{7^2} + \dots$$

- 6 a) Using Laplace transform evaluate 6

$$\int_0^{\infty} e^{-t}(1+2t-t^2+t^3)H(t-1)dt$$

- b) Find inverse Laplace transform of $\tan^{-1}\left(\frac{2}{s^2}\right)$ 6

- c) Find inverse Laplace transform of the following 8

(i) $\frac{1}{s} \tan^{-1}\left(\frac{a}{s}\right)$ (ii) $\frac{(s+1)e^{-s}}{s^2+2s+2}$

7. a) Find inverse Laplace transform of $\frac{1}{(s^2+4s+13)^2}$ by convolution theorem 6

- b) Show that the matrix is a unitary matrix $A = \frac{1}{2} \begin{bmatrix} \sqrt{2} & -i\sqrt{2} & 0 \\ i\sqrt{2} & -\sqrt{2} & 0 \\ 0 & 0 & 2 \end{bmatrix}$ 6

- c) Show that the functions $f_1(x) = 1$; $f_2(x) = x$ are orthogonal on $[-1, 1]$. Determine the constants a and b such that the function $f_3(x) = -1 + ax + bx^2$ is orthogonal to both f_1 and f_2 on that interval. 8

Duration: 3hrs

Maximum Marks: 100

1. Question No.1 and 2 is compulsory.
2. Answer any three from remaining questions.
3. Figures to the right indicate full marks.
4. Assume suitable data if required.

- Q1. a Design single stage RC coupled CE amplifier for the following specifications: 15
 $A_v \geq 150$, $V_{OQ} = 3.6V$, $F_L \leq 20$ Hz, $V_{CC} = 16V$. Use transistor BC147A from data sheet.
 b For the above designed amplifier determine; voltage gain, input impedance, 05
 output impedance and maximum undistorted output voltage.
- Q2. a Design single stage CS amplifier with self-biasing employing JFET type 15
 BFW11 for the following specifications; $A_v \geq 15$, $V_{GS} = 4.0V$, $I_{DSS} = 1.5mA$,
 $V_{DD} = 21V$ and $F_L \leq 20Hz$.
 b For the designed amplifier, determine voltage gain, input impedance, output 05
 impedance and coupling capacitor if two such similar stages are used.
- Q3. a Draw a small signal hybrid parameter equivalent circuit for transistor 10
 amplifier and define the same from characteristics. What are the advantages
 of h-parameters?
 b Design fixed bias with emitter resistance circuit for $I_E = 1.2mA$, $V_{CE} = 4.0V$ 10
 $V_{BE} = 0.7V$ and $\beta = 100$. Assume $V_{CC} = 10V$.
- Q4. a For the amplifier shown in figure.1 analyze and determine 10
 i) Operating point.
 ii) Small-signal mid band voltage gain.
 iii) Input and out put impedance.
 The circuit parameters are: $R_1 = 40k\Omega$, $R_2 = 10k\Omega$, $R_E = 620\Omega$, $R_C = 2.2k\Omega$,
 $V_{CC} = 12V$. The transistor parameters are $\beta = 110$, $V_{BE} = 0.7V$

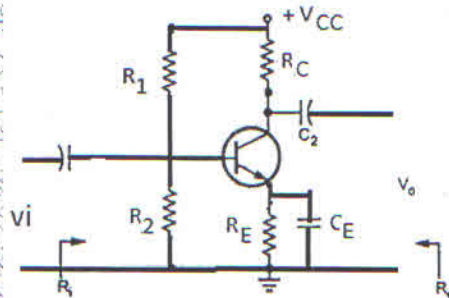


Fig.1

- b Draw JFET small signal common drain amplifier with self-bias and derive the expression for, small signal mid-band voltage gain, input impedance and output impedance. Also write the advantages and disadvantages of this configurations. 10
- Q5 a Draw and explain the construction and working principle for an E-MOSFET. 10
- b Design a JFET voltage divider biasing circuit for CS amplifier. JFET has the following parameters: $I_{DSS} = 3.2 \text{ mA}$, $V_p = -2.5 \text{ V}$. The circuit parameters: $R_D = 1.2 \text{ k}\Omega$, $R_S = 10 \text{ M}\Omega$, $I_{DQ} = 3 \text{ mA}$ and $V_{DS} = 10 \text{ V}$, $V_{DD} = 21 \text{ V}$. Determine the values of R_1 and R_2 . 10
- Q6 a Design L section LC filter with full wave rectifier to meet following specifications: The DC output voltage $V_{DC} = 200 \text{ V}$, deliver $i = 80 \text{ mA} \pm 10 \text{ mA}$ to the resistive load, and required ripple factor is 0.027. Determine output voltage ripple factor for the designed filter circuit. Also find bleeder resistance if required. 12
- b Design a simple Zener voltage regulator to meet the following specifications: Output voltage $V_o = 5 \text{ V}$, Load current $I_{L \text{ max}} = 40 \text{ mA}$, $I_{L \text{ min}} = 1 \text{ mA}$, $I_{Z \text{ max}} = 80 \text{ mA}$, $I_{Z \text{ min}} = 2 \text{ mA}$, $P_Z = 408 \text{ mW}$ and Input voltage $V_i = 15 \text{ V}$ to 25 V . 8
- Q7 Write a short note on following (any two) 20
- SCR (Construction and Characteristics)
 - D C load line for BJT amplifier
 - MOSFET biasing

Transistor type	P _{dm} max @ 25°C Watts	I _{cm} max @ 25°C Amps	V _{ce} (sat) volts d.c.	V _{ce} (sat) volts d.c.	V _{ce} (Sat) volts d.c.	V _{ce} (Sat) volts d.c.	V _{ce} (Sat) volts d.c.	V _{ce} (Sat) volts d.c.	V _{ce} (Sat) volts d.c.	D.C. current		Signal		h _{FE} max.	V _{ce} max.	θ _{JA} °C/W	Derate above 25°C W/°C
										min	typ.	max.	min.				
2N 3055	115.5	15.0	1-1	100	60	70	90	7	200	20	50	15	50	120	1.8	1.5	0.7
ECN 055	50.0	5.0	1-0	60	50	55	60	5	200	25	50	25	75	125	1.5	3.5	0.4
ECN 149	30.0	4.0	1-0	50	40	—	—	8	350	30	50	33	60	115	1.2	4.0	0.3
ECN 100	5.0	0.7	0-6	70	60	65	—	6	200	50	90	50	90	280	0.9	3.5	0.05
BC147A	0.25	0.1	0-25	50	45	50	—	6	125	115	180	125	220	260	0.9	—	—
2N 525(PNP)	0.225	0.5	0-25	85	30	—	—	—	100	35	—	—	45	—	—	—	—
BC147B	0.25	0.1	0-25	50	45	50	—	6	125	200	290	240	330	500	0.9	—	—

BFW 11—JFET MUTUAL CHARACTERISTICS

-V _{GS} volts	I _{DSS} (typ. mA)	I _{DSS} (max. mA)	g _{fs} (typical)	-V _p Volts	r _d	Derate above 25°C	θ _{JA}							
0-0	0-2	0-4	0-6	0-8	1-0	1-2	2-0	2-4	2-5	3-0	3-5	4-0		
I _{DSS} max. mA	10	9-0	8-3	7-6	6-8	6-1	5-4	4-2	3-1	2-2	2-0	1-1	0-5	0-0
I _{DSS} typ. mA	7-0	6-0	5-4	4-6	4-0	3-3	2-7	1-7	0-8	0-2	0-0	0-0	0-0	0-0
I _{DSS} min. mA	4-0	3-0	2-2	1-6	1-0	0-5	0-0	0-0	0-0	0-0	0-0	0-0	0-0	0-0

Transistor type	h _{ic}	h _{oe}	h _{re}	θ _{JA}
BC 147A	2.7 K Ω	18 μ Ω	1.5 × 10 ⁻⁴	0.4°C/mw
2N 525 (PNP)	1.4 K Ω	25 μ Ω	3.2 × 10 ⁻⁴	—
BC 147B	4.5 K Ω	30 μ Ω	2 × 10 ⁻⁴	0.4°C/mw
ECN 100	500 Ω	—	—	—
ECN 149	250 Ω	—	—	—
ECN 055	100 Ω	—	—	—
2N 3055	25 Ω	—	—	—

N-Channel JFET

Type	V _{GS} max. Volts	V _{DS} max. Volts	V _{GS} max. Volts	P _D max. @25°C	T _J max.	I _{DSS}	g _{fs} (typical)	-V _p Volts	r _d	Derate above 25°C	θ _{JA}
2N3822	50	50	50	300 mW	175°C	2 mA	3000 μ D	6	50 KΩ	2 mW/°C	0.59°C/mW
BFW 11 (typical)	30	30	30	300 mW	200°C	7 mA	5600 μ D	2.5	50 KΩ	—	0.59°C/mW